

FORM PTO-1449
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500993.01APPLICATION NO.
10/081,594

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

APPLICANT(S)

Terry L. Gilton

FILING DATE

February 20, 2002

GROUP ART UNIT

2818

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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
MA	AA 5,296,716	03/22/94	Ovshinsky et al.	257	3	
	AB 5,687,112	11/11/97	Ovshinsky	365	163	
	AC 5,761,115	06/02/98	Kozicki et al.	365	182	
	AD 5,869,843	02/09/99	Harshfield	257	5	
	AE 5,896,312	04/20/99	Kozicki et al.	365	153	
	AF 5,912,839	06/15/99	Ovshinsky et al.	365	185.03	
	AG 5,914,893	06/22/99	Kozicki et al.	365	107	
	AH 6,084,796	07/04/00	Kozicki et al.	365	153	
✓	AI 6,150,253	11/21/00	Doan et al.	438	597	
	AJ					

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
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				First Named Inventor	Terry L. Gilton
				Art Unit	2818
				Examiner Name	Not Yet Assigned
Sheet	1		8	Attorney Docket Number	M4065.0627/P627

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)				
MK	AA	US 2002/0168820		11/14/2002	Kozicki et al.	
	AB	6,469,364		10/22/2002	Kozicki	
	AC	6,388,324		05/14/2002	Kozicki et al.	
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	AJ	6,388,324		05/14/2002	Kozicki et al.	
	AK	US 2002/0000666		01/03/2002	Kozicki et al.	
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FOREIGN PATENT DOCUMENTS							
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		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)					
MK	BA	WO 02/21542		03/14/2002	Kozicki et al.		
	BB	WO 00/48196		08/17/2000	Kozicki et al.		
	BC	WO 97/48032		12/18/1997	Kozicki et al.		
	BD	WO 99/28914		06/10/1999	Kozicki et al.		

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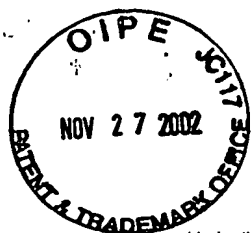
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Sheet	2	of	8	Attorney Docket Number	M4065.0627/P627

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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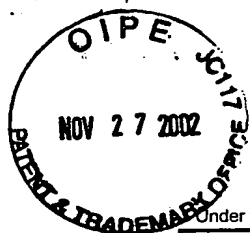
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/081,594
		Filing Date	February 20, 2002
		First Named Inventor	Terry L. Gilton
		Group Art Unit	2818
		Examiner Name	Not Yet Assigned
		Attorney Docket Number	M4065.0627/P627
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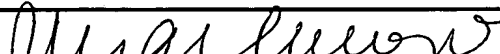
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Filing Date	February 20, 2002
		First Named Inventor	Terry L. Gilton
		Group Art Unit	2818
		Examiner Name	Not Yet Assigned
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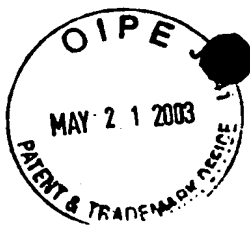
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				Filing Date	February 20, 2002
				First Named Inventor	Terry L. Gilton
				Art Unit	2818
				Examiner Name	Connie C. Yoha
Sheet	1	of	4	Attorney Docket Number	M4065.0726/P726

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
MX	AA	6,469,364	10/2002	Kozicki	
	AB	2002/0168820 App.	11/2002	Kozicki	
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<i>AK</i>	AU1	2002/0190350 APP	12/19/2002	Kozicki	
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	CP			
	CQ			

Examiner Signature		Date Considered	08/03
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